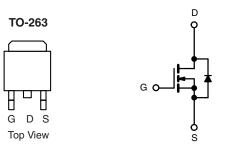


www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	40					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0040					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0055					
I _D (A)	50					
Configuration	Single					



N-Channel MOSFET

FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_q and UIS Tested
- AEC-Q101 Qualified^d
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM50N04-4m0L-GE3

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	s otherwise noted	(b)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	40		
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Currents	T _C = 25 °C		50		
Continuous Drain Current ^a	T _C = 125 °C	l _D	50		
Continuous Source Current (Diode Conducti	I _S	50	Α		
Pulsed Drain Current ^b	I _{DM}	200			
Single Pulse Avalanche Current	gle Pulse Avalanche Current			62	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	192	mJ	
	T _C = 25 °C		150	W	
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	50		
Operating Junction and Storage Temperatur	T _J , T _{stq}	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL	LIMIT	UNIT			
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	°C/W			
Junction-to-Case (Drain)		R _{thJC}	1	G/W			

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					'	ı		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	1	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0025	0.0040	Ω	
Dunin Course On Otata Basistanas		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0067		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0082		
		V _{GS} = 4.5 V	V _{GS} = 4.5 V I _D = 20 A		0.0030	0.0055		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		-	110	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz		4880	6100	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		=.	560	700		
Reverse Transfer Capacitance	C _{rss}]		=.	250	315		
Total Gate Charge ^c	Qg			-	85	130		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 50 \text{ A}$	=.	14	-	nC	
Gate-Drain Charge ^c	Q _{gd}]		=.	14	-		
Gate Resistance	R _g	f = 1 MHz		1	2.15	3.3	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	9	14		
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_L = 0.4 \Omega$ $I_D \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	11	17	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	39	59		
Fall Time ^c	t _f			-	11	17		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	200	Α	
		$I_F = 50 \text{ A}, V_{GS} = 0 \text{ V}$					V	

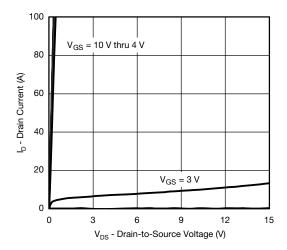
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

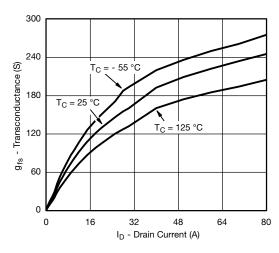
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



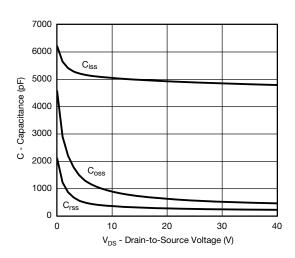
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



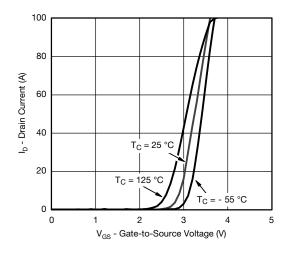
Output Characteristics



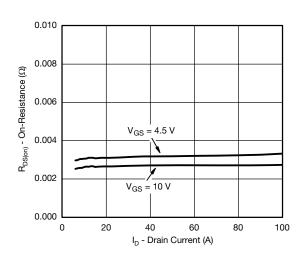
Transconductance



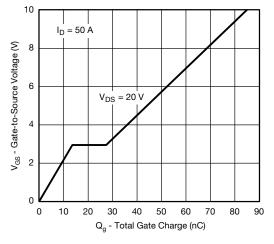
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current

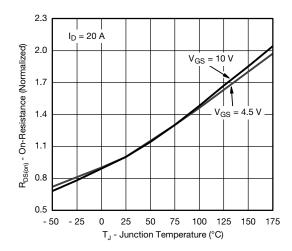


Gate Charge

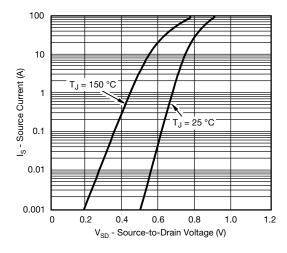
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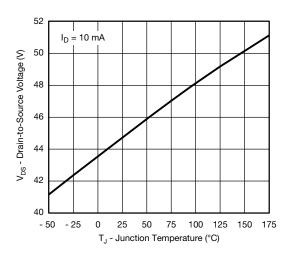
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



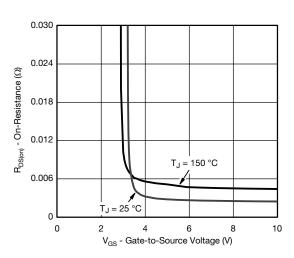
On-Resistance vs. Junction Temperature



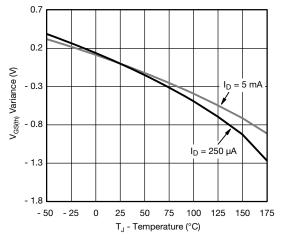
Source Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature



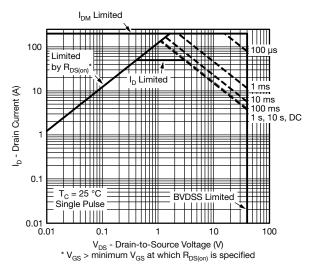
On-Resistance vs. Gate-to-Source Voltage



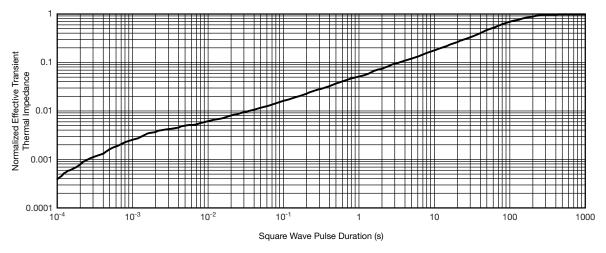
Threshold Voltage

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



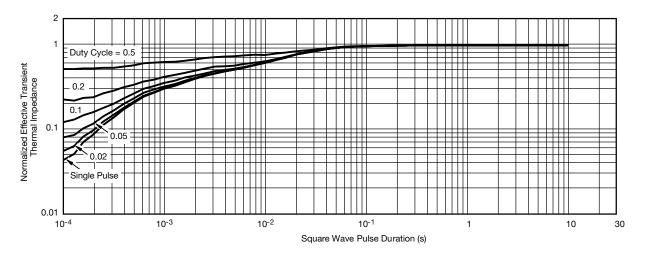
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?66800.



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



⋝:	,	 	b— b1–		ļ	ļ
2:	П				5	ပ
	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

		INCHES		MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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